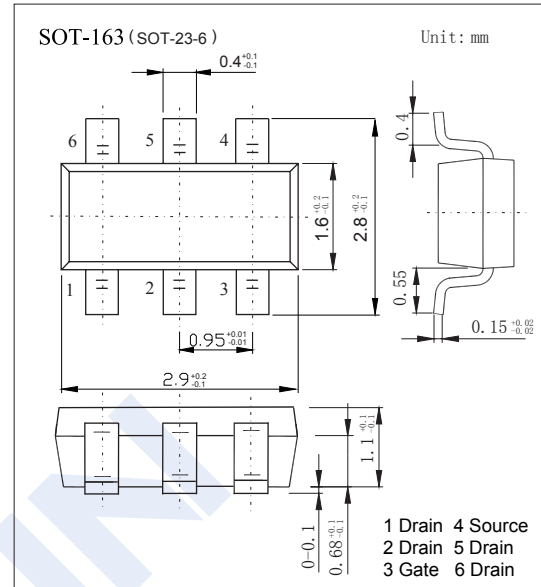
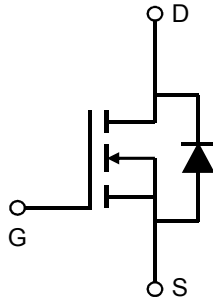


N-Channel MOSFET

AO6420 (KO6420)

■ Features

- $V_{DS} (V) = 60V$
- $I_D = 4.2 A (V_{GS} = 10V)$
- $R_{DS(ON)} < 60m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 75m\Omega (V_{GS} = 4.5V)$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	$T_A = 25^\circ C$	A
		$T_A = 70^\circ C$	
Pulsed Drain Current	I_{DM}	20	
Power Dissipation	P_D	$T_A = 25^\circ C$	W
		$T_A = 70^\circ C$	
Thermal Resistance.Junction- to-Ambient	R_{thJA}	$t \leq 10s$	$^\circ C/W$
		Steady-State	
Thermal Resistance.Junction- to-Lead	R_{thJL}	40	
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

N-Channel MOSFET

AO6420 (KO6420)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μA, V _{GS} =0V	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{Ds} =60V, V _{Gs} =0V			1	μA
		V _{Ds} =60V, V _{Gs} =0V, T _J =55°C			5	
Gate-Body Leakage Current	I _{GSS}	V _{Ds} =0V, V _{Gs} =±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{Ds} =V _{Gs} , I _D =250 μA	1		3	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{Gs} =10V, I _D =4.2A			60	mΩ
		V _{Gs} =10V, I _D =4.2A T _J =125°C		85		
		V _{Gs} =4.5V, I _D =3A			75	
On State Drain Current	I _{D(on)}	V _{Gs} =10V, V _{Ds} =5V	20			A
Forward Transconductance	g _{FS}	V _{Ds} =5V, I _D =4.2A		13		S
Input Capacitance	C _{iss}	V _{Gs} =0V, V _{Ds} =30V, f=1MHz		450	540	pF
Output Capacitance	C _{oss}			60		
Reverse Transfer Capacitance	C _{rss}			25		
Gate Resistance	R _g	V _{Gs} =0V, V _{Ds} =0V, f=1MHz		1.65	2	Ω
Total Gate Charge (10V)	Q _g	V _{Gs} =10V, V _{Ds} =30V, I _D =4.2A		9.5	11.5	nC
Total Gate Charge (4.5V)				4.3	5.5	
Gate Source Charge			Q _{gs}		1.6	
Gate Drain Charge	Q _{gd}			2.2		
Turn-On DelayTime	t _{d(on)}		V _{Gs} =10V, V _{Ds} =30V, R _L =7 Ω, R _G =3 Ω		5.1	
Turn-On Rise Time	t _r			2.6	4	
Turn-Off DelayTime	t _{d(off)}			15.9	20	
Turn-Off Fall Time	t _f			2	3	
Body Diode Reverse Recovery Time	t _{rr}	I _F = 4.2A, di/dt= 100A/us		25.1	35	ns
Body Diode Reverse Recovery Charge	Q _{rr}			28.7		
Maximum Body-Diode Continuous Current	I _S				3	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{Gs} =0V			1	V

* The static characteristics in Figures 1 to 6 are obtained using <300us pulses, duty cycle 0.5% max.

■ Marking

Marking	DN**
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N-Channel MOSFET AO6420 (KO6420)

■ Typical Characteristics

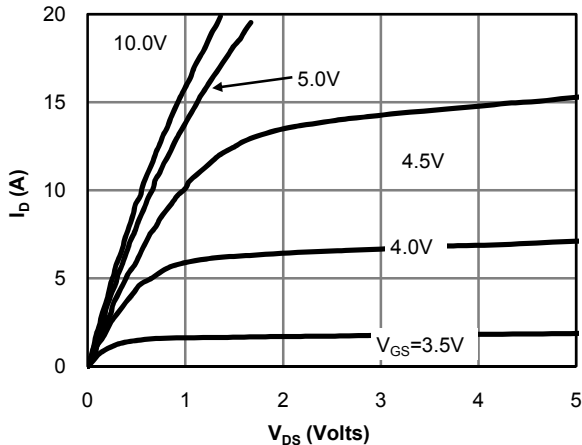


Fig 1: On-Region Characteristics

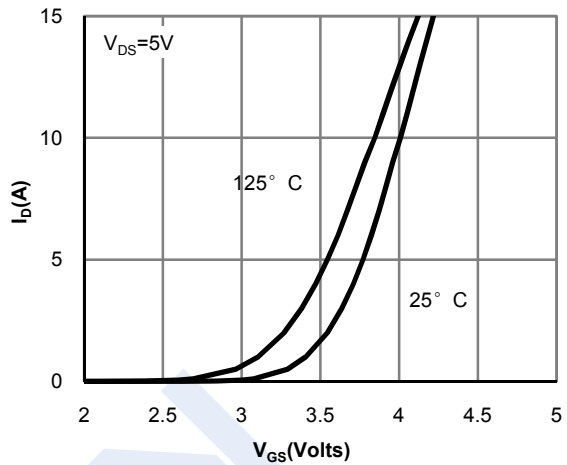


Figure 2: Transfer Characteristics

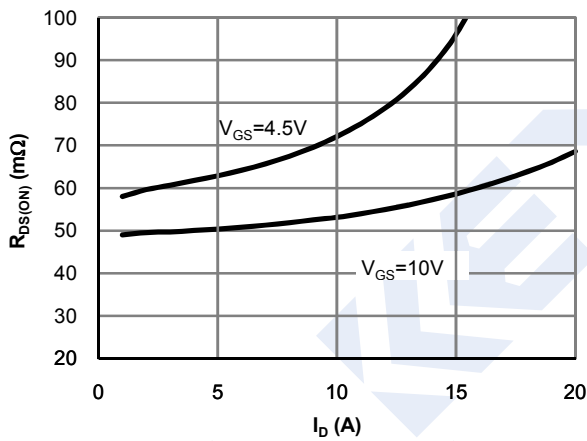


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

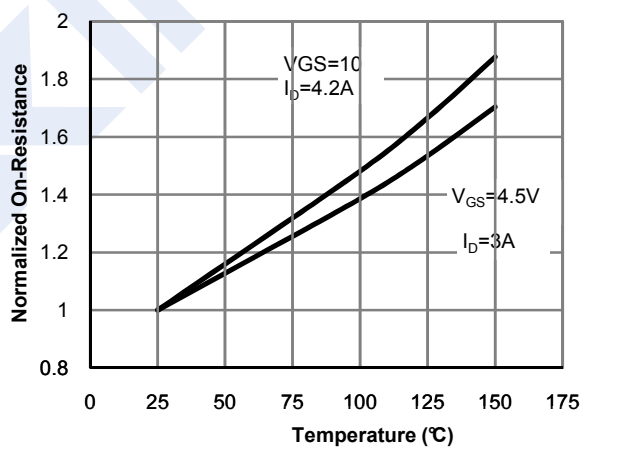


Figure 4: On-Resistance vs. Junction Temperature

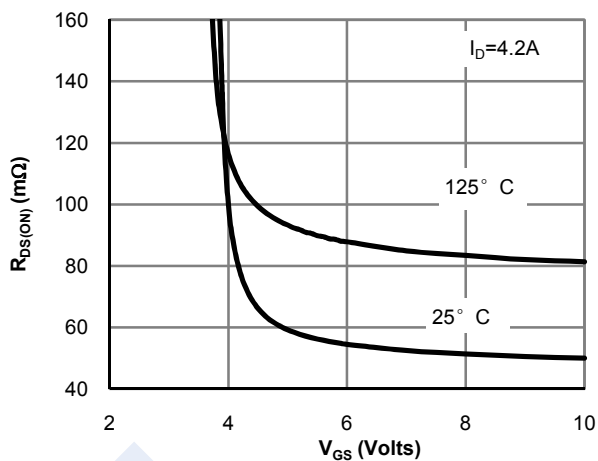


Figure 5: On-Resistance vs. Gate-Source Voltage

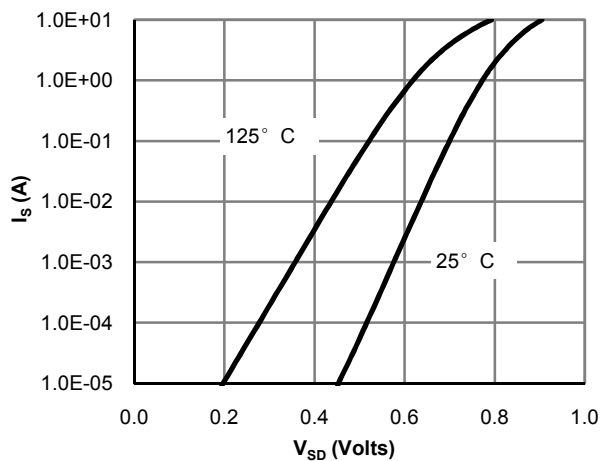


Figure 6: Body-Diode Characteristics

N-Channel MOSFET AO6420 (KO6420)

■ Typical Characteristics

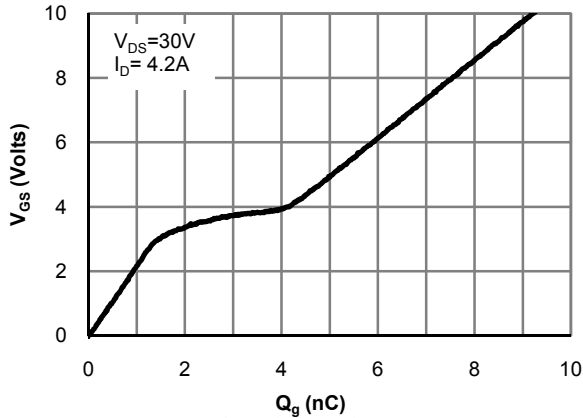


Figure 7: Gate-Charge Characteristics

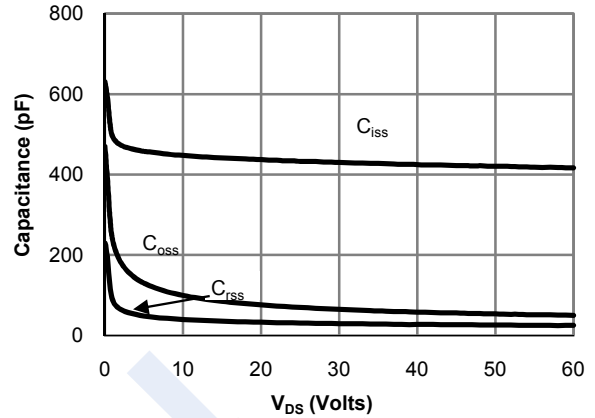


Figure 8: Capacitance Characteristics

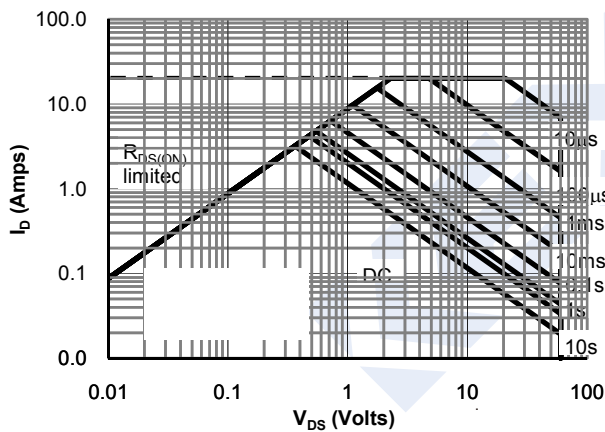


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

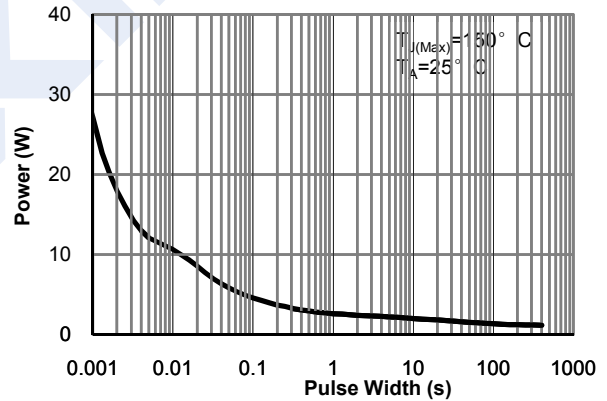


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

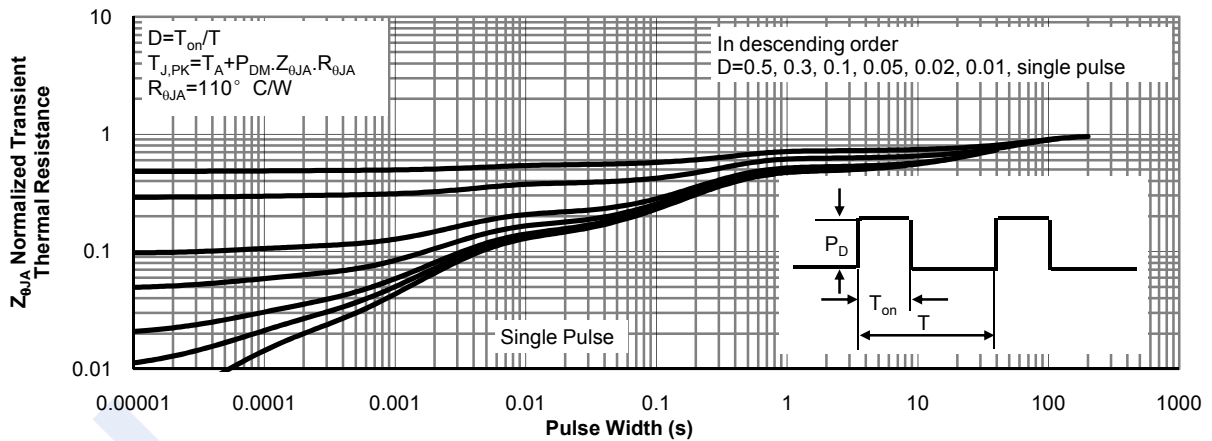


Figure 11: Normalized Maximum Transient Thermal Impedance